

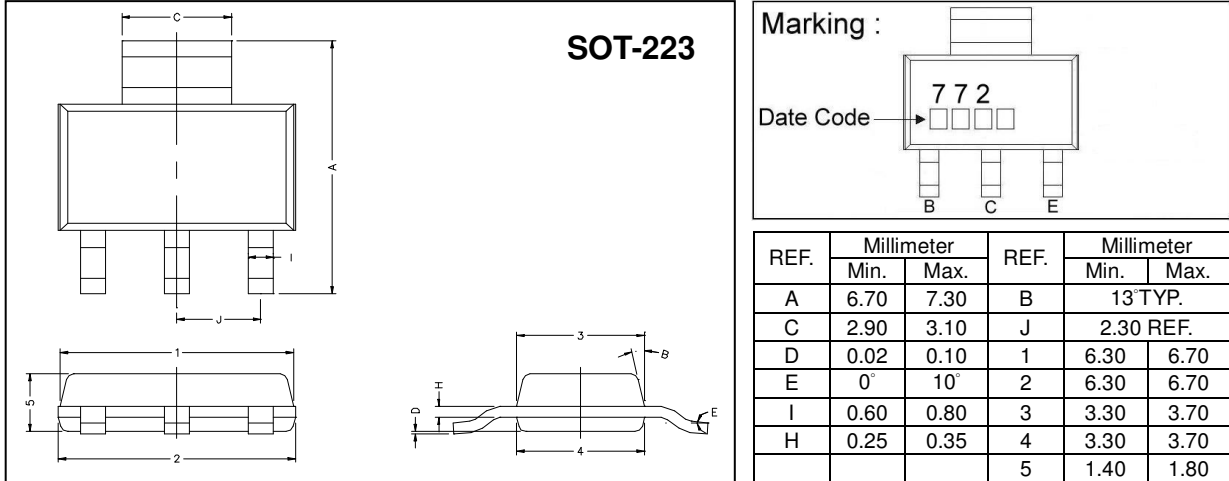
GL772

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The GL772 is designed for using in output stage of 2W amplifier, voltage regulator, DC-DC converter and driver.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage at Ta=25°C	VCBO	-40	V
Collector to Emitter Voltage at Ta=25°C	VCEO	-30	V
Emitter to Base Voltage at Ta=25°C	VEBO	-5.0	V
Collector Current at Ta=25°C	IC	-3.0	A
Total Power Dissipation at Ta=25°C	PD	1.5	W

Characteristics at Ta = 25°C

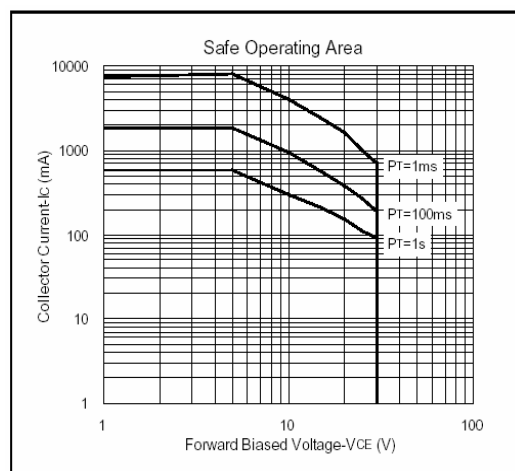
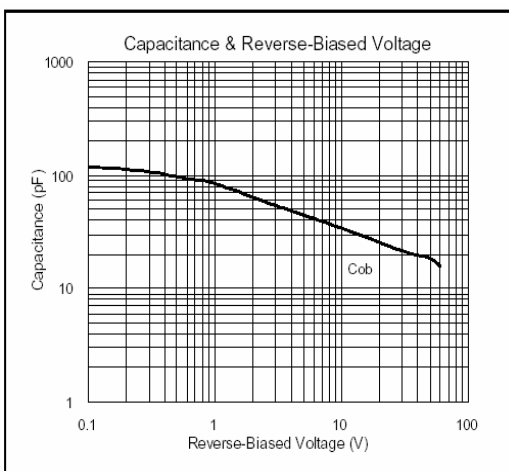
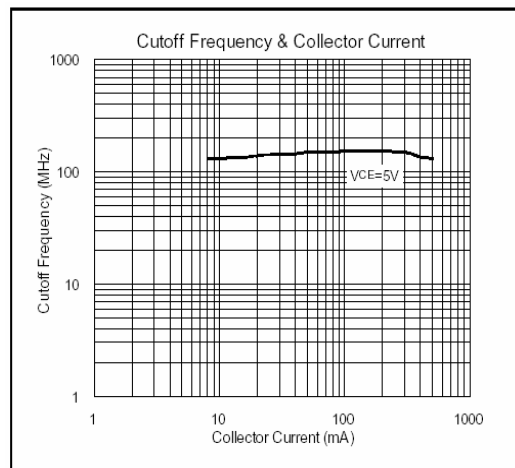
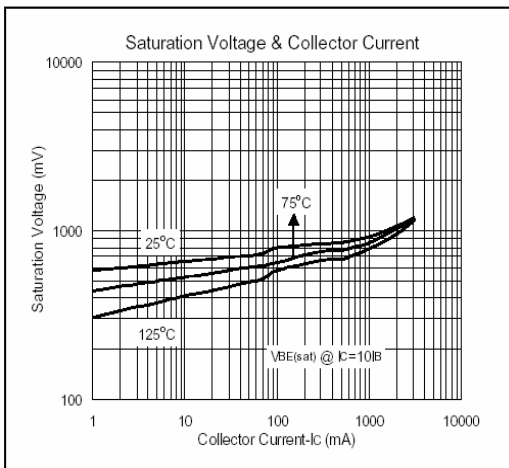
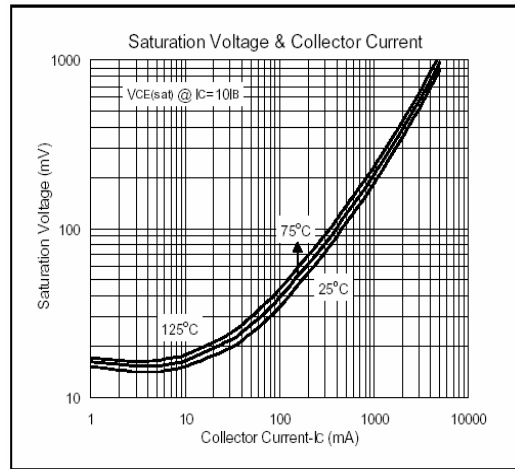
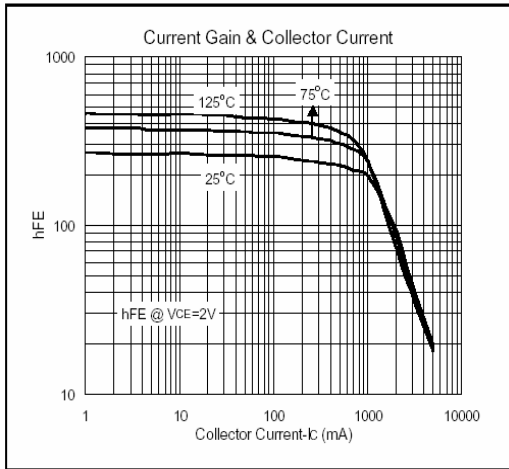
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-40	-	-	V	IC=-100uA
BVCEO	-30	-	-	V	IC=-10mA
BVEBO	-5	-	-	V	IE=-10uA
ICBO	-	-	-1	μA	VCB=-30V
IEBO	-	-	-1	μA	VEB=-3V
*VCE(sat)	-	-0.3	-0.5	V	IC=-2A, IB=-0.2A
*VBE(sat)	-	-1	-2	V	IC=-2A, IB=-0.2A
*hFE1	30	-	-		VCE=-2V, IC=-20mA
*hFE2	100	160	500		VCE=-2V, IC=-1A
fT	-	80	-	MHz	VCE=-20V, IC=-20mA, f=100MHz
Cob	-	55	-	pF	VCB=-10V, f=1MHz

*Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Classification Of hFE2

Rank	Q	P	E
Range	100-200	160-320	250-500

Characteristics Curve



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